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3	BRS	L3	5175	(bias same dependence)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:32
4	BRS	L4	242	(bias adj dependence)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:33
5	BRS	L5	11	(bias adj dependence) same temperature same process	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:35

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6	BRS	L6	90	(semiconductor) and (bias adj dependence) and (temperature) and process	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:36
7	BRS	L7	3	(semiconductor) and (bias adj dependence) and (temperature) and process and (lay adj out)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:47
8	BRS	L8	45194	(semiconductor) same subsequent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:47
9	BRS	L9	5	((semiconductor) same subsequent) and (s-parameter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:48
10	BRS	L10	1	((semiconductor) same subsequent) and (s-parameter) and SEM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:48

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11	BRS	L11	3	((semiconductor) same subsequent) and (s-parameter) and (semiconductor same characteristics)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:48
12	BRS	L12	3	((semiconductor) same subsequent) and (s-parameter) and (semiconductor same characteristics) and fabrication	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:51
13	BRS	L13	1	((semiconductor) same subsequent) and (equivalent adj model) and (semiconductor same characteristics) and fabrication	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:51
14	BRS	L14	2	((semiconductor) same subsequent) and (equivalent adj model) and fabrication	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:51
15	BRS	L15	85	((semiconductor) same subsequent) and (equivalent same model) and fabrication	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:52

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	4	((semiconductor) same subsequent) and (equivalent same model same fabrication)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:55
17	BRS	L17	163	(equivalent same model same fabrication)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:55
18	BRS	L18	1	((equivalent adj model) same fabrication)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:55
19	BRS	L19	100	((equivalent adj model) and fabrication)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:56
20	BRS	L20	16	((equivalent adj model) same semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:56

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21	BRS	L21	0	((equivalent adj model) same semiconductor) and subsequejt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 09:57
22	BRS	L22	5	((equivalent adj model) same semiconductor) and subsequent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 10:29
23	BRS	L23	2	"5878053".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 10:31
24	BRS	L24	1	"5878053".pn. and average	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 10:42
25	BRS	L25	1	"5878053".pn. and characteristics	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 11:03

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26	BRS	L26	1	"5878053".pn. and sample	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/29 11:03

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